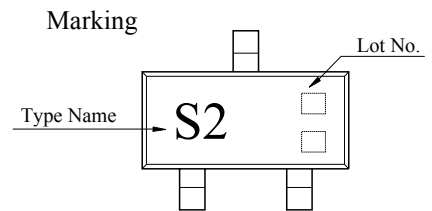
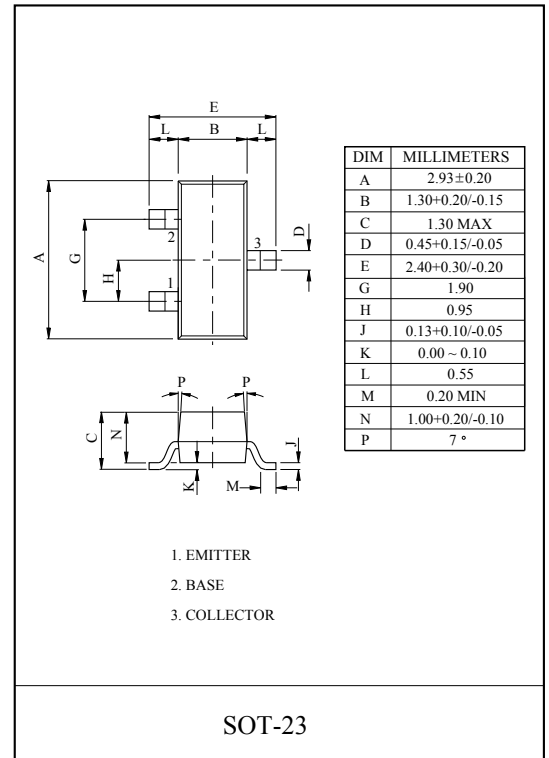


HIGH FREQUENCY APPLICATION.  
VHF BAND AMPLIFIER APPLICATION.

### MAXIMUM RATING (Ta=25°C)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Collector-Base Voltage	$V_{CBO}$	30	V
Collector-Emitter Voltage	$V_{CEO}$	15	V
Emitter-Base Voltage	$V_{EBO}$	3	V
Collector Current	$I_C$	100	mA
Emitter Current	$I_E$	-100	mA
Collector Power Dissipation	$P_C$	200	mW
Junction Temperature	$T_j$	150	°C
Storage Temperature Range	$T_{stg}$	-65 ~ 150	°C



### ELECTRICAL CHARACTERISTICS (Ta=25°C)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	$I_C=3mA, I_B=0$	15	-	-	V
Collector-Base Breakdown Voltage	$V_{(BR)CBO}$	$I_C=1\mu A, I_E=0$	30	-	-	V
Emitter-Base Breakdown Voltage	$V_{(BR)EBO}$	$I_E=10\mu A, I_C=0$	3.0	-	-	V
Collector Cut-off Current	$I_{CBO}$	$V_{CB}=15V, I_E=0$	-	-	10	nA
DC Current Gain	$h_{FE}$	$V_{CE}=1V, I_C=3mA$	20	-	-	
Base-Emitter Saturation Voltage	$V_{BE(sat)}$	$I_C=10mA, I_B=1mA$	-	-	1.0	V
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C=10mA, I_B=1mA$	-	-	0.4	V
Transition Frequency	$f_T$	$I_C=4mA, V_{CE}=10V, f=100MHz$	600	-	-	MHz
Collector Input Capacitance	$C_{ib}$	$V_{EB}=0.5V, I_C=0, f=1MHz$	-	-	2.0	pF
Collector Output Capacitance	$C_{ob}$	$V_{CB}=0V, I_E=0, f=1MHz$	-	-	3.0	pF
		$V_{CB}=10V, I_E=0, f=1MHz$	-	-	1.7	
Noise Figure	NF	$V_{CE}=6V, I_C=1mA,$ $R_g=400\Omega, f=60MHz$	-	-	6.0	dB